



# BFU520Y

Dual NPN wideband silicon RF transistor

Rev. 1 — 20 February 2014

Product data sheet

## 1. Product profile

### 1.1 General description

Dual NPN silicon RF transistor for high speed, low noise applications in a plastic, 6-pin SOT363 package.

The BFU520Y is part of the BFU5 family of transistors, suitable for small signal to medium power applications up to 2 GHz.

### 1.2 Features and benefits

- Low noise, high breakdown RF transistor
- AEC-Q101 qualified
- Minimum noise figure ( $NF_{min}$ ) = 0.65 dB at 900 MHz
- Maximum stable gain 19 dB at 900 MHz
- 11 GHz  $f_T$  silicon technology

### 1.3 Applications

- Applications requiring high supply voltages and high breakdown voltages
- Broadband differential amplifiers up to 2 GHz
- Low noise amplifiers for ISM applications
- ISM band oscillators

### 1.4 Quick reference data

**Table 1. Quick reference data**

$T_{amb} = 25\text{ °C}$  unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CB}$	collector-base voltage	open emitter	-	-	24	V
$V_{CE}$	collector-emitter voltage	open base	-	-	12	V
		shorted base	-	-	24	V
$V_{EB}$	emitter-base voltage	open collector	-	-	2	V
$I_C$	collector current		-	5	30	mA
$P_{tot}$	total power dissipation	$T_{sp} \leq 87\text{ °C}$	[1]	-	450	mW
$h_{FE}$	DC current gain	$I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$	60	95	200	
$C_c$	collector capacitance	$V_{CB} = 8\text{ V}$ ; $f = 1\text{ MHz}$	-	0.48	-	pF
$f_T$	transition frequency	$I_C = 10\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 900\text{ MHz}$	-	10	-	GHz



**Table 1. Quick reference data ...continued**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$G_{p(max)}$	maximum power gain	$I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 900\text{ MHz}$	[2]	19	-	dB
$NF_{min}$	minimum noise figure	$I_C = 1\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 900\text{ MHz}$ ; $\Gamma_S = \Gamma_{opt}$	-	0.65	-	dB
$P_{L(1dB)}$	output power at 1 dB gain compression	$I_C = 10\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $Z_S = Z_L = 50\text{ }\Omega$ ; $f = 900\text{ MHz}$	-	7.0	-	dBm

[1]  $T_{sp}$  is the temperature at the solder point of the collector lead.

[2] If  $K > 1$  then  $G_{p(max)}$  is the maximum power gain. If  $K < 1$  then  $G_{p(max)} = MSG$ .

## 2. Pinning information

**Table 2. Discrete pinning**

Pin	Description	Simplified outline	Graphic symbol
1	base1		
2	emitter1		
3	collector2		
4	base2		
5	emitter2		
6	collector1		

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
BFU520Y	-	plastic surface-mounted package; 6 leads	SOT363

## 4. Marking

**Table 4. Marking**

Type number	Marking	Description
BFU520Y	WB*	* = t : made in Malaysia * = w : made in China

## 5. Design support

**Table 5. Available design support**

Download from the BFU520Y product information page on <http://www.nxp.com>.

Support item	Available	Remarks
Device models for Agilent EEsof EDA ADS	yes	Based on Mextram device model.
SPICE model	yes	Based on Gummel-Poon device model.
S-parameters	yes	
Noise parameters	yes	
Solder pattern	yes	

## 6. Limiting values

**Table 6. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CB}$	collector-base voltage	open emitter	-	30	V
$V_{CE}$	collector-emitter voltage	open base	-	16	V
		shorted base	-	30	V
$V_{EB}$	emitter-base voltage	open collector	-	3	V
$I_C$	collector current		-	50	mA
$T_{stg}$	storage temperature		-65	+150	°C
$V_{ESD}$	electrostatic discharge voltage	Human Body Model (HBM) According to JEDEC standard 22-A114E	-	±150	V
		Charged Device Model (CDM) According to JEDEC standard 22-C101B	-	±2	kV

## 7. Recommended operating conditions

**Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CB}$	collector-base voltage	open emitter	-	-	24	V
$V_{CE}$	collector-emitter voltage	open base	-	-	12	V
		shorted base	-	-	24	V
$V_{EB}$	emitter-base voltage	open collector	-	-	2	V
$I_C$	collector current		-	-	30	mA
$P_i$	input power	$Z_S = 50 \Omega$	-	-	10	dBm
$T_j$	junction temperature		-40	-	+150	°C
$P_{tot}$	total power dissipation	$T_{sp} \leq 87 \text{ °C}$	[1]	-	450	mW

[1]  $T_{sp}$  is the temperature at the solder point of the collector lead.

## 8. Thermal characteristics

**Table 8. Thermal characteristics**

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[1] 140	K/W

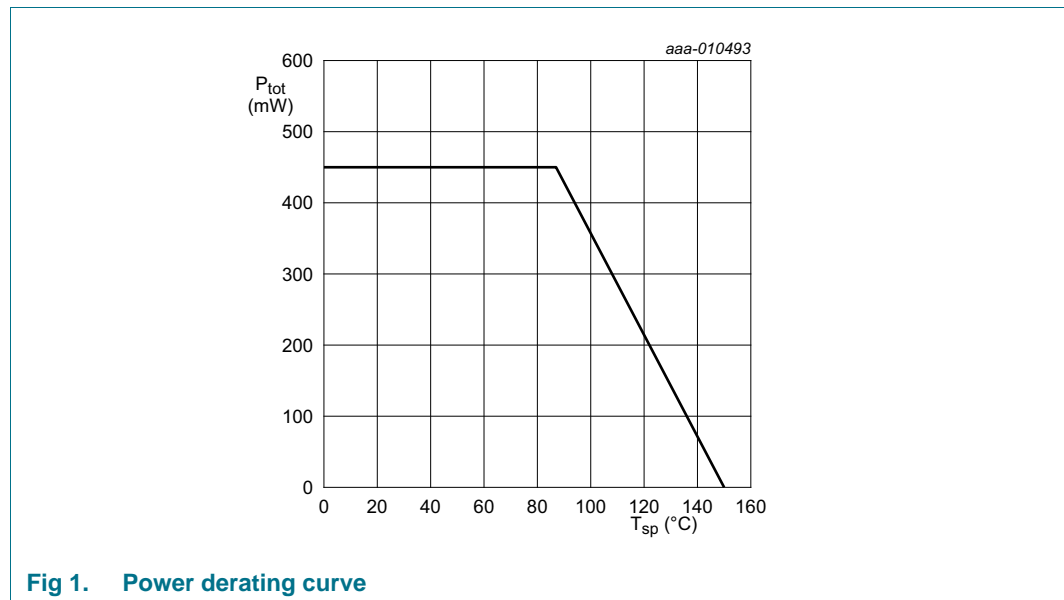
[1]  $T_{sp}$  is the temperature at the solder point of the collector lead.

$T_{sp}$  has the following relation to the ambient temperature  $T_{amb}$ :

$$T_{sp} = T_{amb} + P \times R_{th(sp-a)}$$

With P being the power dissipation and  $R_{th(sp-a)}$  being the thermal resistance between the solder point and ambient.  $R_{th(sp-a)}$  is determined by the heat transfer properties in the application.

The heat transfer properties are set by the application board materials, the board layout and the environment e.g. housing.



**Fig 1. Power derating curve**

## 9. Characteristics

**Table 9. Characteristics**

$T_{amb} = 25\text{ °C}$  unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100\text{ nA}$ ; $I_E = 0\text{ mA}$	24	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 150\text{ nA}$ ; $I_B = 0\text{ mA}$	12	-	-	V
$I_C$	collector current		-	5	30	mA
$I_{CBO}$	collector-base cut-off current	$I_E = 0\text{ mA}$ ; $V_{CB} = 8\text{ V}$	-	<1	-	nA
$h_{FE}$	DC current gain	$I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$	60	95	200	
$C_e$	emitter capacitance	$V_{EB} = 0.5\text{ V}$ ; $f = 1\text{ MHz}$	-	0.64	-	pF
$C_{re}$	feedback capacitance	$V_{CE} = 8\text{ V}$ ; $f = 1\text{ MHz}$	-	0.30	-	pF
$C_c$	collector capacitance	$V_{CB} = 8\text{ V}$ ; $f = 1\text{ MHz}$	-	0.48	-	pF
$f_T$	transition frequency	$I_C = 10\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 900\text{ MHz}$	-	10	-	GHz

**Table 9. Characteristics ...continued**  
 $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

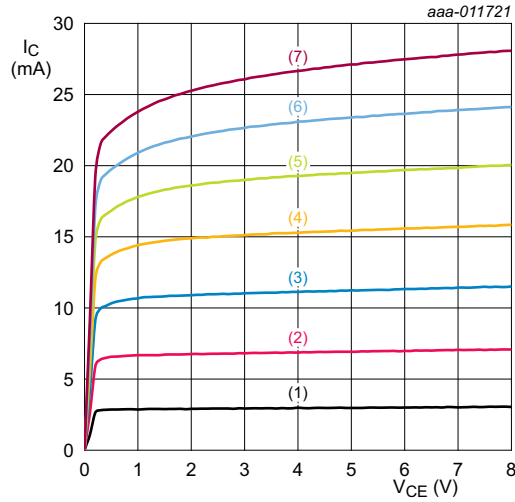
Symbol	Parameter	Conditions	Min	Typ	Max	Unit		
$G_{p(max)}$	maximum power gain	$f = 433\text{ MHz}; V_{CE} = 8\text{ V}$	[1]					
		$I_C = 1\text{ mA}$	-	16.5	-	dB		
		$I_C = 5\text{ mA}$	-	23	-	dB		
		$I_C = 10\text{ mA}$	-	24	-	dB		
		$f = 900\text{ MHz}; V_{CE} = 8\text{ V}$	[1]					
		$I_C = 1\text{ mA}$	-	14.5	-	dB		
		$I_C = 5\text{ mA}$	-	19	-	dB		
		$I_C = 10\text{ mA}$	-	20	-	dB		
		$f = 1800\text{ MHz}; V_{CE} = 8\text{ V}$	[1]					
		$I_C = 1\text{ mA}$	-	11.5	-	dB		
		$I_C = 5\text{ mA}$	-	14.5	-	dB		
		$I_C = 10\text{ mA}$	-	14	-	dB		
		$ S_{21} ^2$	insertion power gain	$f = 433\text{ MHz}; V_{CE} = 8\text{ V}$				
				$I_C = 1\text{ mA}$	-	10.5	-	dB
				$I_C = 5\text{ mA}$	-	20	-	dB
$I_C = 10\text{ mA}$	-			22	-	dB		
$f = 900\text{ MHz}; V_{CE} = 8\text{ V}$								
$I_C = 1\text{ mA}$	-			9	-	dB		
$I_C = 5\text{ mA}$	-			16	-	dB		
$I_C = 10\text{ mA}$	-			17	-	dB		
$f = 1800\text{ MHz}; V_{CE} = 8\text{ V}$								
$I_C = 1\text{ mA}$	-			6.5	-	dB		
$I_C = 5\text{ mA}$	-			11	-	dB		
$I_C = 10\text{ mA}$	-			11.5	-	dB		
$NF_{min}$	minimum noise figure			$f = 433\text{ MHz}; V_{CE} = 8\text{ V}; \Gamma_S = \Gamma_{opt}$				
				$I_C = 1\text{ mA}$	-	0.6	-	dB
				$I_C = 5\text{ mA}$	-	0.7	-	dB
		$I_C = 10\text{ mA}$	-	0.9	-	dB		
		$f = 900\text{ MHz}; V_{CE} = 8\text{ V}; \Gamma_S = \Gamma_{opt}$						
		$I_C = 1\text{ mA}$	-	0.65	-	dB		
		$I_C = 5\text{ mA}$	-	0.8	-	dB		
		$I_C = 10\text{ mA}$	-	0.95	-	dB		
		$f = 1800\text{ MHz}; V_{CE} = 8\text{ V}; \Gamma_S = \Gamma_{opt}$						
		$I_C = 1\text{ mA}$	-	0.8	-	dB		
		$I_C = 5\text{ mA}$	-	0.85	-	dB		
		$I_C = 10\text{ mA}$	-	1.0	-	dB		

**Table 9. Characteristics ...continued**  
 $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit		
$G_{ass}$	associated gain	$f = 433\text{ MHz}; V_{CE} = 8\text{ V}; \Gamma_S = \Gamma_{opt}$						
		$I_C = 1\text{ mA}$	-	25	-	dB		
		$I_C = 5\text{ mA}$	-	24	-	dB		
		$I_C = 10\text{ mA}$	-	24	-	dB		
		$f = 900\text{ MHz}; V_{CE} = 8\text{ V}; \Gamma_S = \Gamma_{opt}$						
		$I_C = 1\text{ mA}$	-	17	-	dB		
		$I_C = 5\text{ mA}$	-	18	-	dB		
		$I_C = 10\text{ mA}$	-	18	-	dB		
		$f = 1800\text{ MHz}; V_{CE} = 8\text{ V}; \Gamma_S = \Gamma_{opt}$						
		$I_C = 1\text{ mA}$	-	10.5	-	dB		
		$I_C = 5\text{ mA}$	-	12	-	dB		
		$I_C = 10\text{ mA}$	-	12.5	-	dB		
$P_{L(1dB)}$	output power at 1 dB gain compression	$f = 433\text{ MHz}; V_{CE} = 8\text{ V}; Z_S = Z_L = 50\text{ }\Omega$						
		$I_C = 5\text{ mA}$	-	1	-	dBm		
		$I_C = 10\text{ mA}$	-	6	-	dBm		
		$f = 900\text{ MHz}; V_{CE} = 8\text{ V}; Z_S = Z_L = 50\text{ }\Omega$						
		$I_C = 5\text{ mA}$	-	2	-	dBm		
		$I_C = 10\text{ mA}$	-	7	-	dBm		
		$f = 1800\text{ MHz}; V_{CE} = 8\text{ V}; Z_S = Z_L = 50\text{ }\Omega$						
		$I_C = 5\text{ mA}$	-	4	-	dBm		
		$I_C = 10\text{ mA}$	-	8.5	-	dBm		
		$IP_{3o}$	output third-order intercept point	$f_1 = 433\text{ MHz}; f_2 = 434\text{ MHz}; V_{CE} = 8\text{ V}; Z_S = Z_L = 50\text{ }\Omega$				
				$I_C = 5\text{ mA}$	-	10	-	dBm
				$I_C = 10\text{ mA}$	-	16	-	dBm
$f_1 = 900\text{ MHz}; f_2 = 901\text{ MHz}; V_{CE} = 8\text{ V}; Z_S = Z_L = 50\text{ }\Omega$								
$I_C = 5\text{ mA}$	-			11	-	dBm		
$I_C = 10\text{ mA}$	-			17	-	dBm		
$f_1 = 1800\text{ MHz}; f_2 = 1801\text{ MHz}; V_{CE} = 8\text{ V}; Z_S = Z_L = 50\text{ }\Omega$								
$I_C = 5\text{ mA}$	-			14	-	dBm		
$I_C = 10\text{ mA}$	-			18	-	dBm		

[1] If  $K > 1$  then  $G_{p(max)}$  is the maximum power gain. If  $K < 1$  then  $G_{p(max)} = MSG$ .

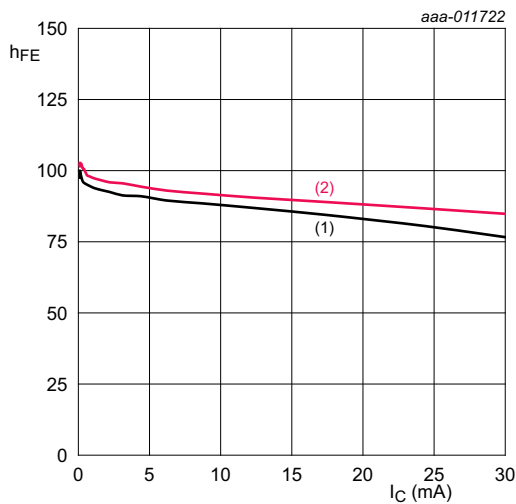
9.1 Graphs



$T_{amb} = 25\text{ }^\circ\text{C}$ .

- (1)  $I_B = 25\text{ }\mu\text{A}$
- (2)  $I_B = 75\text{ }\mu\text{A}$
- (3)  $I_B = 125\text{ }\mu\text{A}$
- (4)  $I_B = 175\text{ }\mu\text{A}$
- (5)  $I_B = 225\text{ }\mu\text{A}$
- (6)  $I_B = 275\text{ }\mu\text{A}$
- (7)  $I_B = 325\text{ }\mu\text{A}$

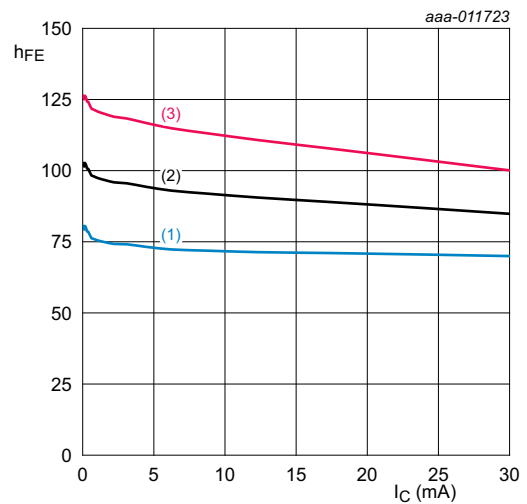
Fig 2. Collector current as a function of collector-emitter voltage; typical values



$T_{amb} = 25\text{ }^\circ\text{C}$ .

- (1)  $V_{CE} = 3.0\text{ V}$
- (2)  $V_{CE} = 8.0\text{ V}$

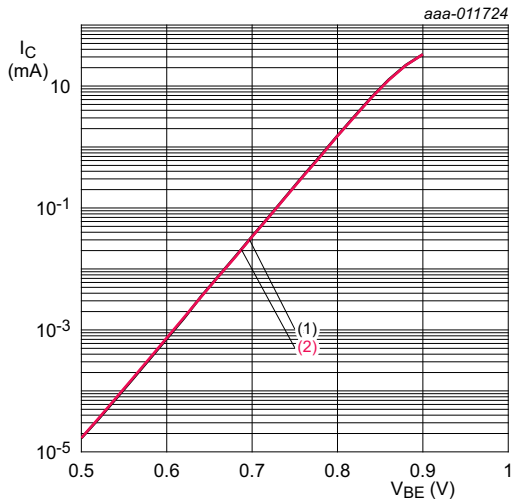
Fig 3. DC current gain as function of collector current; typical values



$V_{CE} = 8\text{ V}$ .

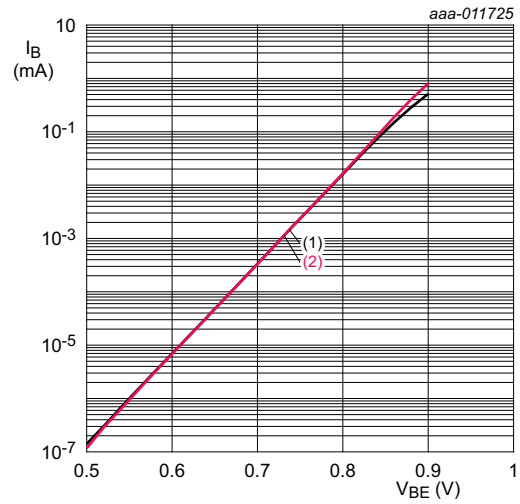
- (1)  $T_{amb} = -40\text{ }^\circ\text{C}$
- (2)  $T_{amb} = +25\text{ }^\circ\text{C}$
- (3)  $T_{amb} = +125\text{ }^\circ\text{C}$

Fig 4. DC current gain as function of collector current; typical values



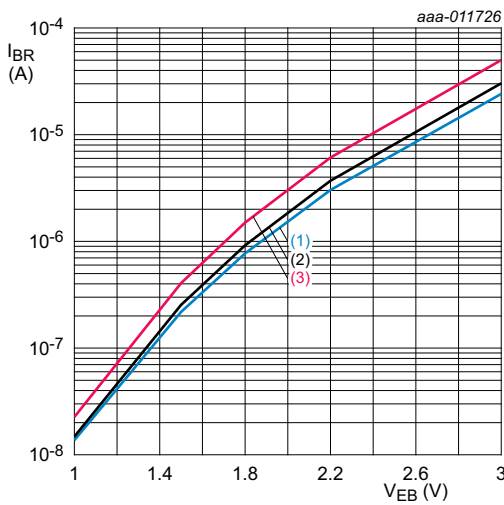
$T_{amb} = 25\text{ }^{\circ}\text{C}.$   
 (1)  $V_{CE} = 3.0\text{ V}$   
 (2)  $V_{CE} = 8.0\text{ V}$

**Fig 5. Collector current as a function of base-emitter voltage; typical values**



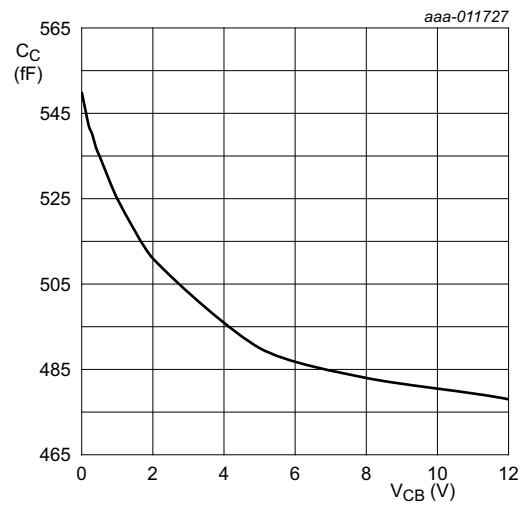
$T_{amb} = 25\text{ }^{\circ}\text{C}.$   
 (1)  $V_{CE} = 3.0\text{ V}$   
 (2)  $V_{CE} = 8.0\text{ V}$

**Fig 6. Base current as a function of base-emitter voltage; typical values**



$V_{CE} = 3\text{ V}.$   
 (1)  $T_{amb} = -40\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = +25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = +125\text{ }^{\circ}\text{C}$

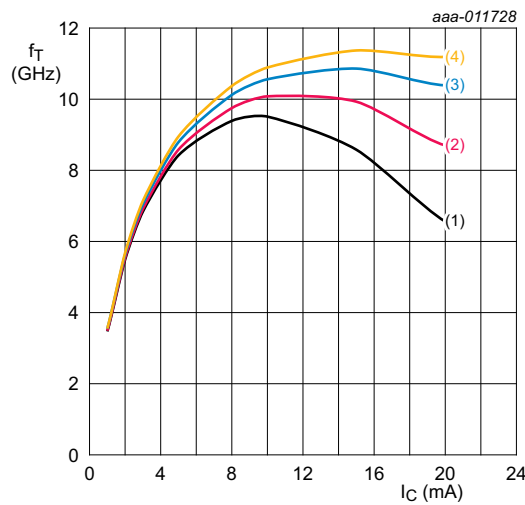
**Fig 7. Reverse base current as a function of emitter-base voltage; typical values**



$I_C = 0\text{ mA}; f = 1\text{ MHz}; T_{amb} = 25\text{ }^{\circ}\text{C}.$

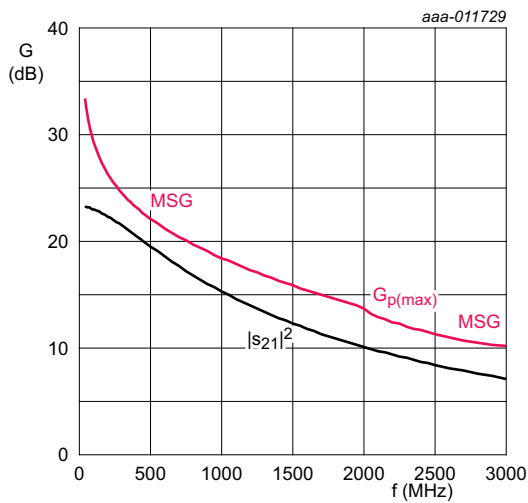
**Fig 8. Collector capacitance as a function of collector-base voltage; typical values**





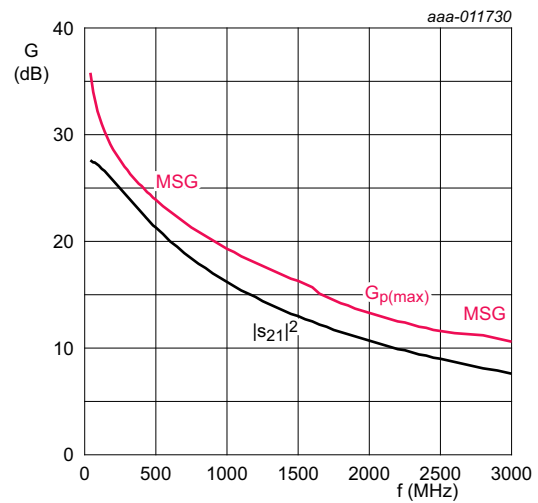
- $T_{amb} = 25\text{ }^\circ\text{C}$ .
- (1)  $V_{CE} = 3.3\text{ V}$
  - (2)  $V_{CE} = 5.0\text{ V}$
  - (3)  $V_{CE} = 8.0\text{ V}$
  - (4)  $V_{CE} = 12.0\text{ V}$

Fig 9. Transition frequency as a function of collector current; typical values



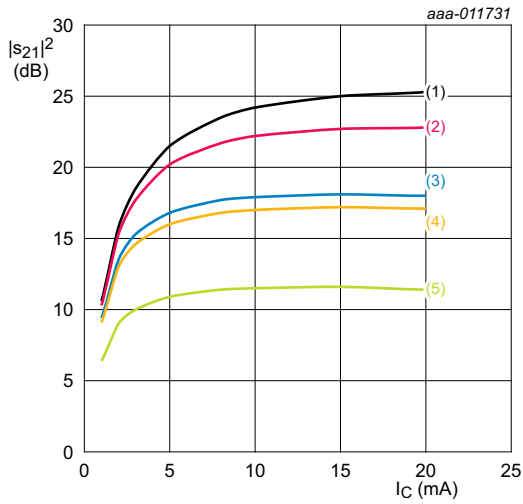
$I_C = 5\text{ mA}$ ;  $V_{CE} = 8\text{ V}$ ;  $T_{amb} = 25\text{ }^\circ\text{C}$ .

Fig 10. Gain as a function of frequency; typical values



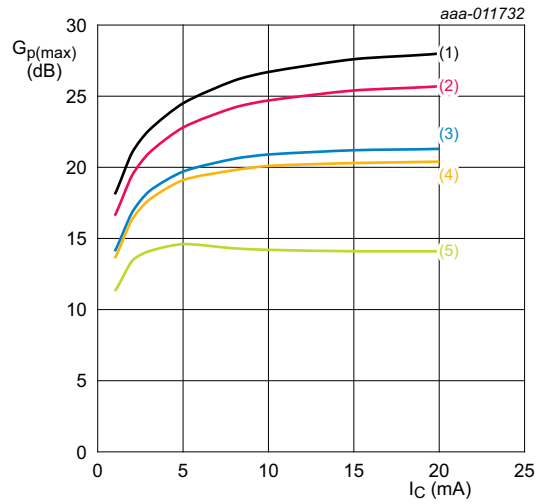
$I_C = 10\text{ mA}$ ;  $V_{CE} = 8\text{ V}$ ;  $T_{amb} = 25\text{ }^\circ\text{C}$ .

Fig 11. Gain as a function of frequency; typical values



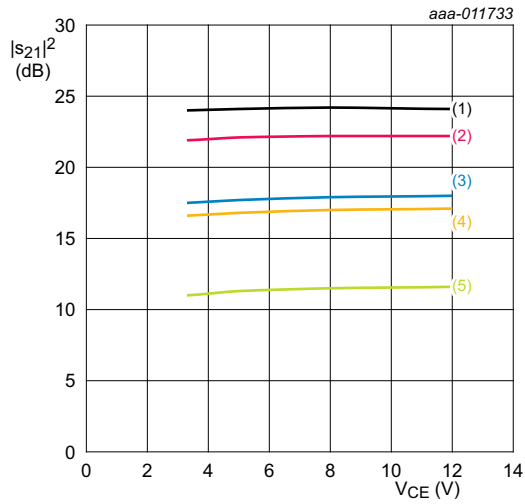
$V_{CE} = 8\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}.$   
 (1)  $f = 300\text{ MHz}$   
 (2)  $f = 433\text{ MHz}$   
 (3)  $f = 800\text{ MHz}$   
 (4)  $f = 900\text{ MHz}$   
 (5)  $f = 1800\text{ MHz}$

**Fig 12. Insertion power gain as a function of collector current; typical values**



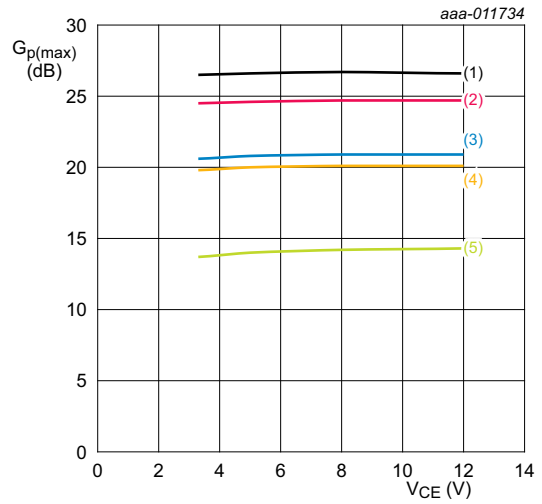
$V_{CE} = 8\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}.$   
 If  $K > 1$  then  $G_{p(max)}$  = maximum power gain. If  $K < 1$  then  $G_{p(max)}$  = MSG.  
 (1)  $f = 300\text{ MHz}$   
 (2)  $f = 433\text{ MHz}$   
 (3)  $f = 800\text{ MHz}$   
 (4)  $f = 900\text{ MHz}$   
 (5)  $f = 1800\text{ MHz}$

**Fig 13. Maximum power gain as a function of collector current; typical values**



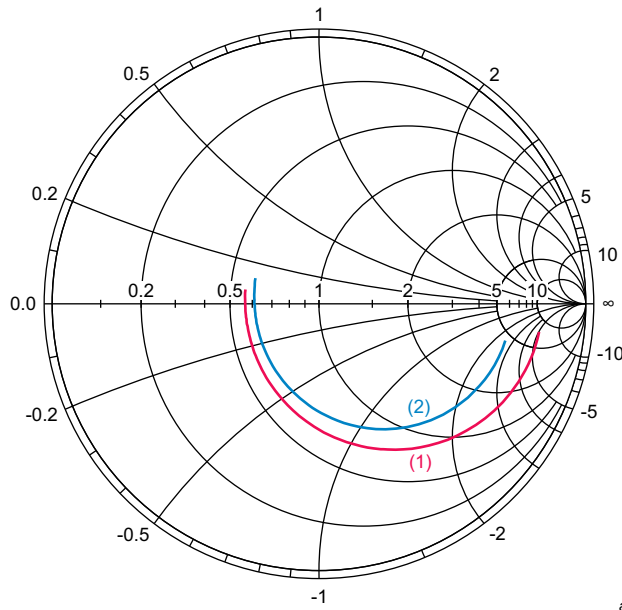
$I_C = 10 \text{ mA}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}.$   
 (1)  $f = 300 \text{ MHz}$   
 (2)  $f = 433 \text{ MHz}$   
 (3)  $f = 800 \text{ MHz}$   
 (4)  $f = 900 \text{ MHz}$   
 (5)  $f = 1800 \text{ MHz}$

**Fig 14. Insertion power gain as a function of collector-emitter voltage; typical values**



$I_C = 10 \text{ mA}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}.$   
 If  $K > 1$  then  $G_{p(\text{max})}$  = maximum power gain. If  $K < 1$  then  $G_{p(\text{max})}$  = MSG.  
 (1)  $f = 300 \text{ MHz}$   
 (2)  $f = 433 \text{ MHz}$   
 (3)  $f = 800 \text{ MHz}$   
 (4)  $f = 900 \text{ MHz}$   
 (5)  $f = 1800 \text{ MHz}$

**Fig 15. Maximum power gain as a function of collector-emitter voltage; typical values**

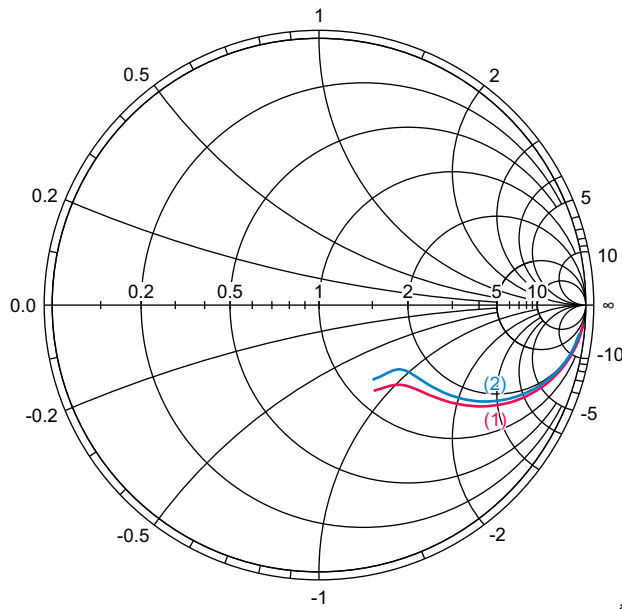


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$V_{CE} = 8\text{ V}; 40\text{ MHz} \leq f \leq 3\text{ GHz}.$

- (1)  $I_C = 5\text{ mA}$
- (2)  $I_C = 10\text{ mA}$

**Fig 16. Input reflection coefficient ( $s_{11}$ ); typical values**

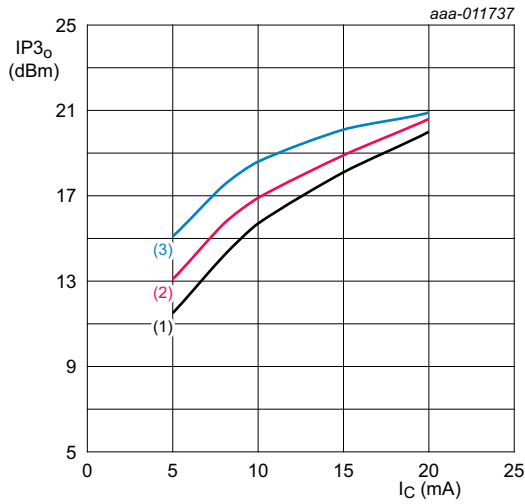


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$V_{CE} = 8\text{ V}; 40\text{ MHz} \leq f \leq 3\text{ GHz}.$

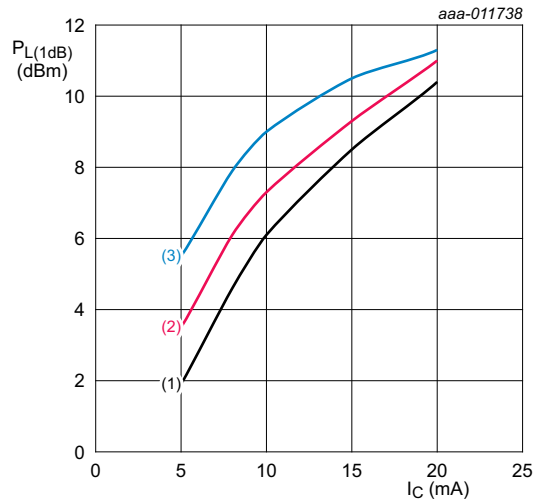
- (1)  $I_C = 5\text{ mA}$
- (2)  $I_C = 10\text{ mA}$

**Fig 17. Output reflection coefficient ( $s_{22}$ ); typical values**



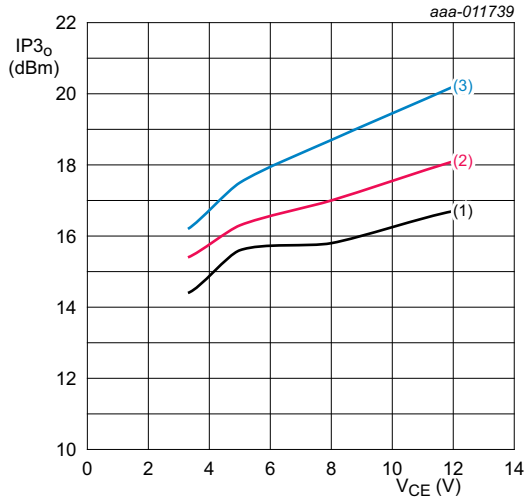
$V_{CE} = 8\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}.$   
 (1)  $f_1 = 433\text{ MHz}; f_2 = 434\text{ MHz}$   
 (2)  $f_1 = 900\text{ MHz}; f_2 = 901\text{ MHz}$   
 (3)  $f_1 = 1800\text{ MHz}; f_2 = 1801\text{ MHz}$

**Fig 18. Output third-order intercept point as a function of collector current; typical values**



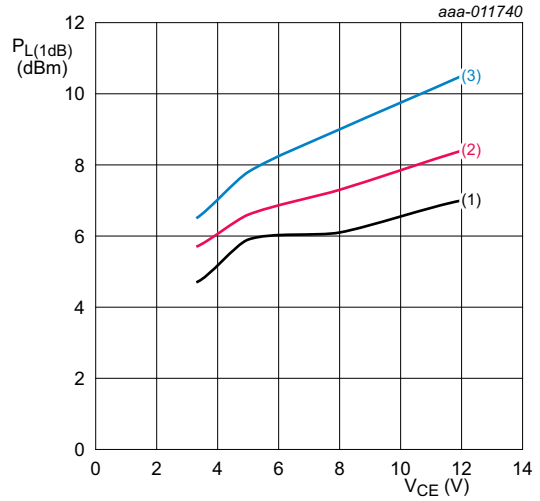
$V_{CE} = 8\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}.$   
 (1)  $f = 433\text{ MHz}$   
 (2)  $f = 900\text{ MHz}$   
 (3)  $f = 1800\text{ MHz}$

**Fig 19. Output power at 1 dB gain compression as a function of collector current; typical values**



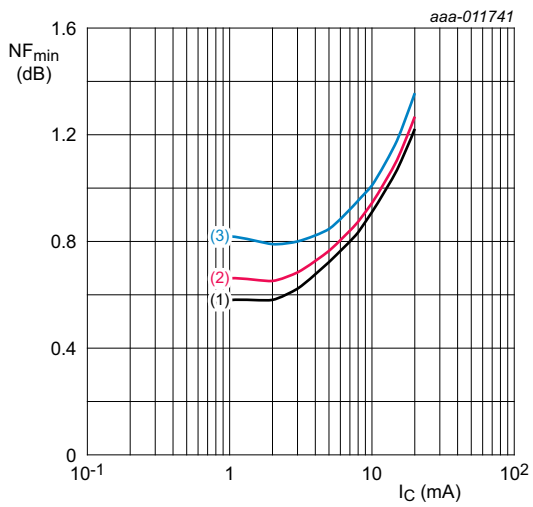
$I_C = 10\text{ mA}; T_{amb} = 25\text{ }^{\circ}\text{C}.$   
 (1)  $f_1 = 433\text{ MHz}; f_2 = 434\text{ MHz}$   
 (2)  $f_1 = 900\text{ MHz}; f_2 = 901\text{ MHz}$   
 (3)  $f_1 = 1800\text{ MHz}; f_2 = 1801\text{ MHz}$

**Fig 20. Output third-order intercept point as a function of collector-emitter voltage; typical values**



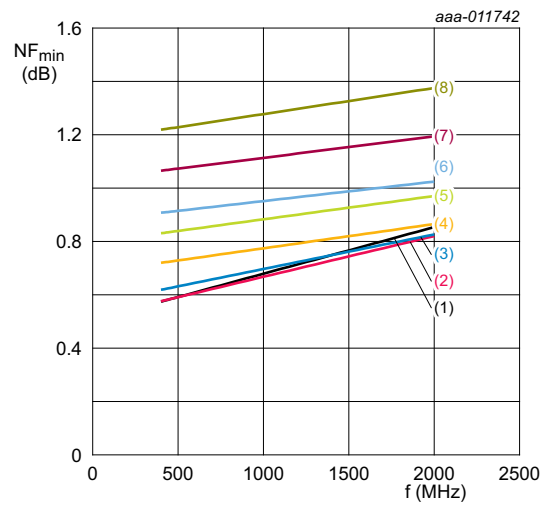
$I_C = 10\text{ mA}; T_{amb} = 25\text{ }^{\circ}\text{C}.$   
 (1)  $f = 433\text{ MHz}$   
 (2)  $f = 900\text{ MHz}$   
 (3)  $f = 1800\text{ MHz}$

**Fig 21. Output power at 1 dB gain compression as a function of collector-emitter voltage; typical values**



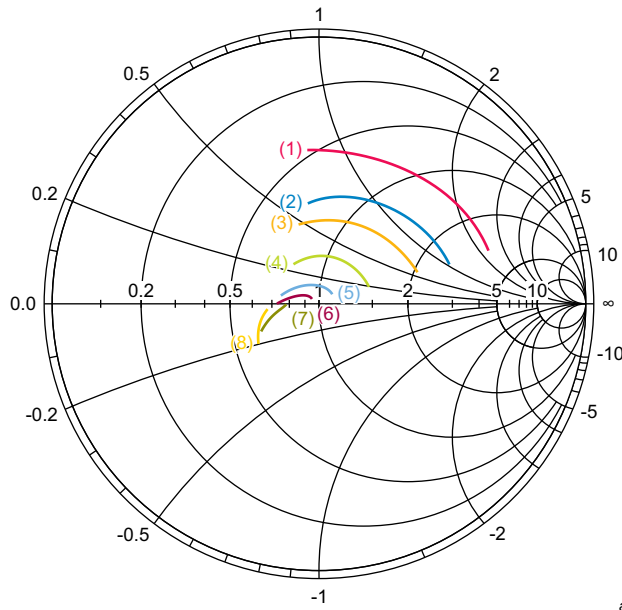
V<sub>CE</sub> = 8 V; T<sub>amb</sub> = 25 °C; Γ<sub>S</sub> = Γ<sub>opt</sub>.  
 (1) f = 433 MHz  
 (2) f = 900 MHz  
 (3) f = 1800 MHz

**Fig 22. Minimum noise figure as a function of collector current; typical values**



V<sub>CE</sub> = 8 V; T<sub>amb</sub> = 25 °C; Γ<sub>S</sub> = Γ<sub>opt</sub>.  
 (1) I<sub>C</sub> = 1 mA  
 (2) I<sub>C</sub> = 2 mA  
 (3) I<sub>C</sub> = 3 mA  
 (4) I<sub>C</sub> = 5 mA  
 (5) I<sub>C</sub> = 8 mA  
 (6) I<sub>C</sub> = 10 mA  
 (7) I<sub>C</sub> = 15 mA  
 (8) I<sub>C</sub> = 20 mA

**Fig 23. Minimum noise figure as a function of frequency; typical values**



$V_{CE} = 8 \text{ V}; 400 \text{ MHz} \leq f \leq 2 \text{ GHz}.$

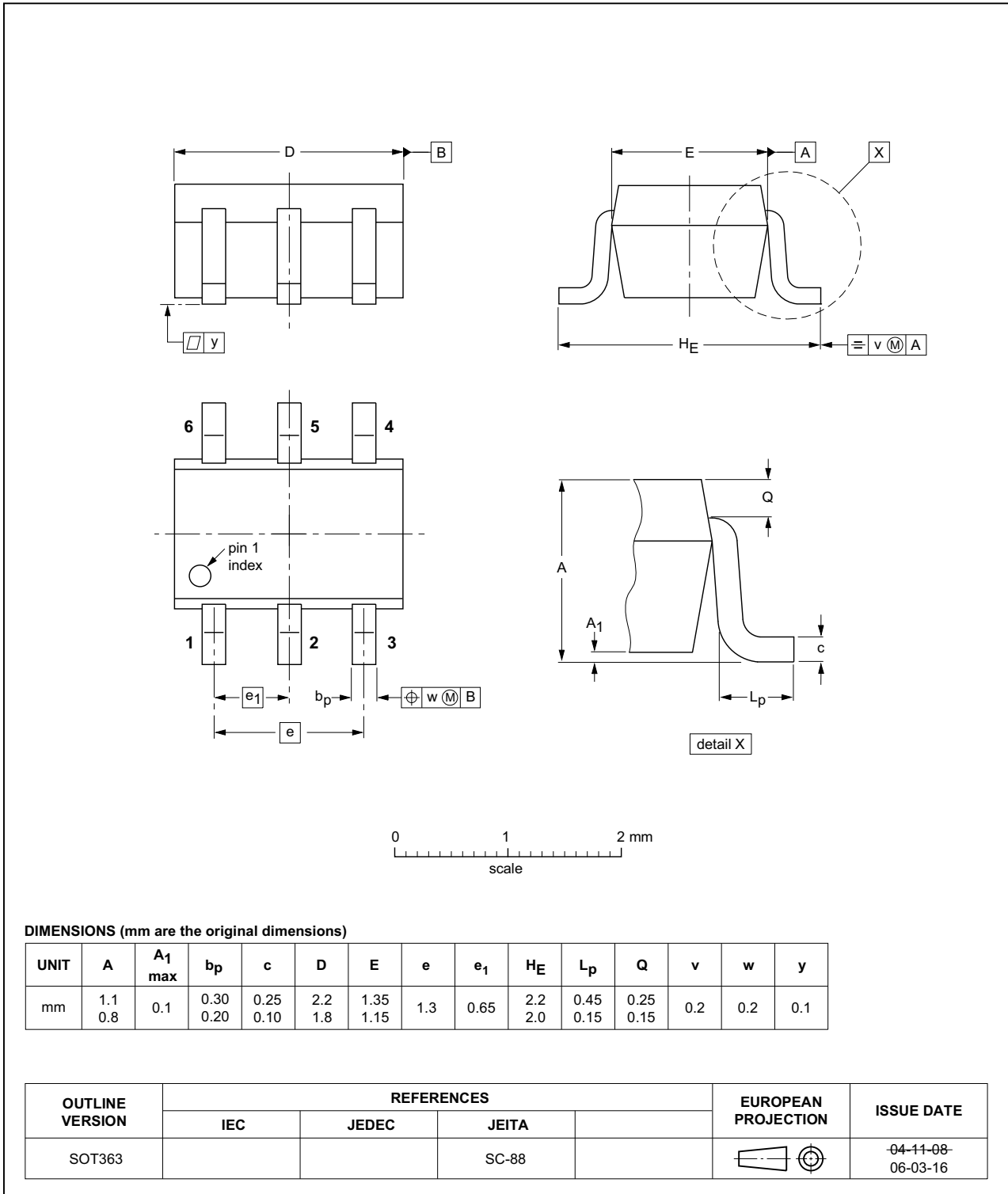
- (1)  $I_C = 1 \text{ mA}$
- (2)  $I_C = 2 \text{ mA}$
- (3)  $I_C = 3 \text{ mA}$
- (4)  $I_C = 5 \text{ mA}$
- (5)  $I_C = 8 \text{ mA}$
- (6)  $I_C = 10 \text{ mA}$
- (7)  $I_C = 15 \text{ mA}$
- (8)  $I_C = 20 \text{ mA}$

**Fig 24. Optimum reflection coefficient ( $\Gamma_{opt}$ ); typical values**

**10. Package outline**

Plastic surface-mounted package; 6 leads

SOT363



**Fig 25. Package outline SOT363**



## 11. Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

## 12. Abbreviations

Table 10. Abbreviations

Acronym	Description
AEC	Automotive Electronics Council
ISM	Industrial, Scientific and Medical
LNA	Low-Noise Amplifier
MSG	Maximum Stable Gain
NPN	Negative-Positive-Negative
SMA	SubMiniature version A

## 13. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFU520Y v.1	20140220	Product data sheet	-	-

## 14. Legal information

### 14.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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